

Title (en)
ETCHING SOLUTION AND ETCHING METHOD

Title (de)
ÄTZLÖSUNG UND ÄTZVERFAHREN

Title (fr)
SOLUTION DE GRAVURE ET PROCÉDÉ DE GRAVURE

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Application
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Abstract (en)
[origin: WO2008089733A2] The invention relates to an etching solution (1) comprising water, nitric acid, hydrofluoric acid, and sulphuric acid, containing 15 to 40% by weight of nitric acid, 10 to 41% by weight of sulphuric acid and 0.8 to 2.0% by weight of hydrofluoric acid. The invention also relates to the use of said etching solution for etching silicon and to etching methods for silicon wafers.

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Citation (search report)
See references of WO 2008089733A2

Citation (examination)

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- EP 0496229 A2 19920729 - RIEDEL DE HAEN AG [DE]
- WO 2005093788 A1 20051006 - RENA SONDERMASCHINEN GMBH [DE], et al

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